

Reference signs

100 p-MOS layer sequences  
101 n-MOS layer sequences  
102 layer sequences  
103 silicon substrate  
104 gate oxide layer  
105 undoped polysilicon layer  
106 photoresist  
107 n-type implantation  
110 layer sequence  
111 n-doped polysilicon layer  
112 hard mask  
120 layer sequence  
121 BARC structure  
122 photoresist structure  
130 layer sequence  
131 hard mask structure  
140 CMOS gate stack layer sequence  
141 undoped gate  
142 n-doped gate  
200 p-MOS layer sequences  
201 n-MOS layer sequences  
202 layer sequences  
203 silicon substrate  
204 gate oxide layer  
205 undoped polysilicon layer  
206 photoresist  
207 n-type implantation  
210 layer sequences  
211 n-doped polysilicon layer  
212 hard mask  
213 auxiliary undoped polysilicon layer  
214 photoresist  
215 n-type implantation

220 layer sequences  
221 auxiliary n-doped polysilicon layer  
222 BARC structure  
223 photoresist structure  
230 layer sequences  
231 first laterally confined etching stack  
232 second laterally confined etching stack  
240 CMOS gate stack layer sequence  
241 undoped gate  
242 n-doped gate